

Isc N-Channel MOSFET Transistor

AOD4130

• FEATURES

- With To-252(DPAK) package
- Low input capacitance and gate charge
- Low gate input resistance
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

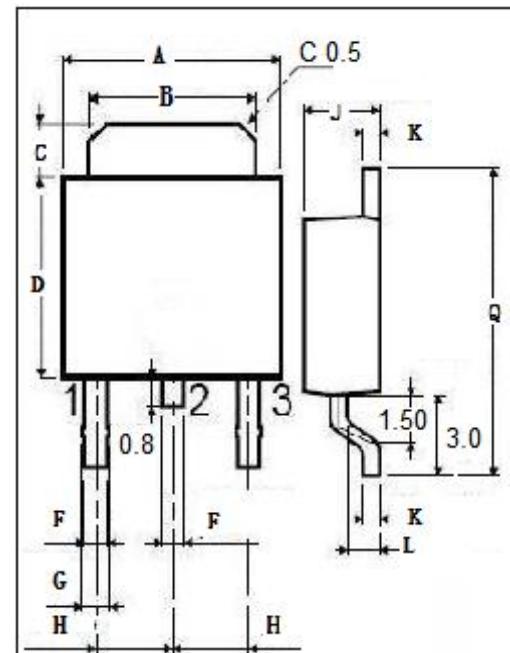
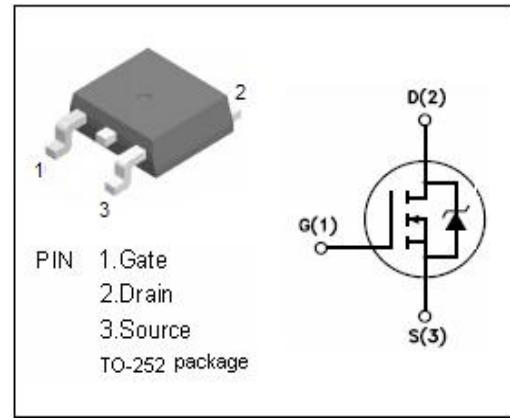
- Switching applications
- Load switch
- Power management

• ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|---|----------|------------------|
| V_{DSS} | Drain-Source Voltage | 60 | V |
| V_{GSS} | Gate-Source Voltage | ± 20 | V |
| I_D | Drain Current-Continuous $T_c=25^\circ\text{C}$ $T_c=100^\circ\text{C}$ | 30 20 | A |
| I_{DM} | Drain Current-Single Pulsed | 74 | A |
| P_D | Total Dissipation @ $T_c=25^\circ\text{C}$ | 52 | W |
| T_j | Max. Operating Junction Temperature | 175 | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature | -55~175 | $^\circ\text{C}$ |

• THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|----------------|---------------------------------------|-----|---------------------------|
| $R_{th(ch-c)}$ | Channel-to-case thermal resistance | 2.9 | $^\circ\text{C}/\text{W}$ |
| $R_{th(ch-a)}$ | Channel-to-ambient thermal resistance | 20 | $^\circ\text{C}/\text{W}$ |



| DIM | mm | |
|-----|------|------|
| | MIN | MAX |
| A | 6.40 | 6.60 |
| B | 5.20 | 5.40 |
| C | 1.15 | 1.35 |
| D | 5.70 | 6.10 |
| E | 0.8 | |
| F | 0.65 | |
| G | 0.75 | |
| H | 2.10 | 2.50 |
| I | 1.50 | |
| J | 2.10 | 2.40 |
| K | 0.40 | 0.60 |
| L | 0.90 | 1.10 |
| M | 3.0 | |
| N | 0.5 | |
| O | 9.90 | 10.1 |

Isc N-Channel MOSFET Transistor**AOD4130****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP | MAX | UNIT |
|---------------------|--------------------------------|--|-----|------|--------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V; I _D = 0.25mA | 60 | | | V |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =±20V; I _D =0.25mA | 1.6 | | 2.8 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D =20A | | 19.5 | 24 | mΩ |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} = ±20V; V _{DS} = 0V | | | ±0.1 | μ A |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} =60V; V _{GS} = 0V; T _c =25°C T _c =55°C | | | 1 5 | μ A |
| V _{SDF} | Diode forward voltage | I _{SD} =1A, V _{GS} = 0 V | | | 1 | V |

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